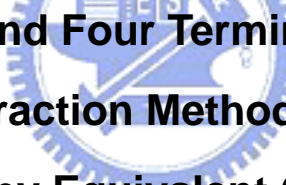


國立交通大學  
電子工程學系 電子研究所  
碩士論文

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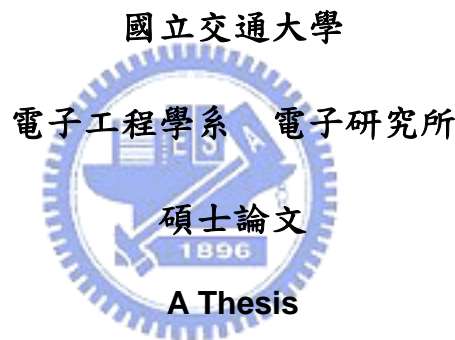
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